

BTA201W series E

1 A Three-quadrant triacs high commutation

Rev. 02 — 17 September 2007

Product data sheet

1. Product profile

1.1 General description

Passivated guaranteed commutation triacs in a surface-mounted plastic package, intended for interfacing with low-power drivers, including microcontrollers.

1.2 Features

- Suitable for interfacing with low-power drivers, including microcontrollers
- SOT223 surface mounted

1.3 Applications

- Motor control
- Solenoid drivers

1.4 Quick reference data

- $I_{TSM} \leq 12.5$ A
- $V_{DRM} \leq 600$ V (BTA201W-600E)
- $V_{DRM} \leq 800$ V (BTA201W-800E)
- $I_{T(RMS)} \leq 1$ A
- $I_{GT} \leq 10$ mA

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)	<p>SOT223</p>	<p>sym051</p>
2	main terminal 2 (T2)		
3	gate (G)		
4	main terminal 2 (T2)		

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BTA201W-600E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BTA201W-800E			

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage	BTA201W-600E	[1] -	600	V
		BTA201W-800E	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 106 °C; see Figure 4 and 5	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _j = 25 °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	12.5	A
		t = 16.7 ms	-	13.7	A
I ² t	I ² t for fusing	t = 10 ms	-	0.78	A ² s
di _T /dt	rate of rise of on-state current	I _{TM} = 1.5 A; I _G = 0.2 A; di _G /dt = 0.2 A/μs	-	100	A/μs
I _{GM}	peak gate current		-	2	A
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	+150	°C
T _j	junction temperature		-	125	°C

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/μs.

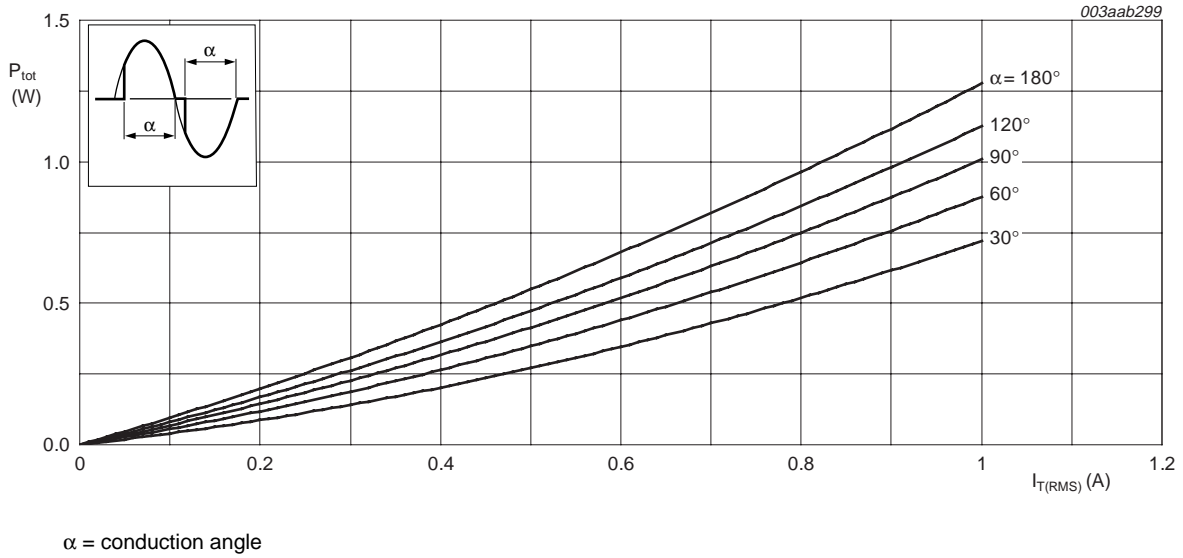


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

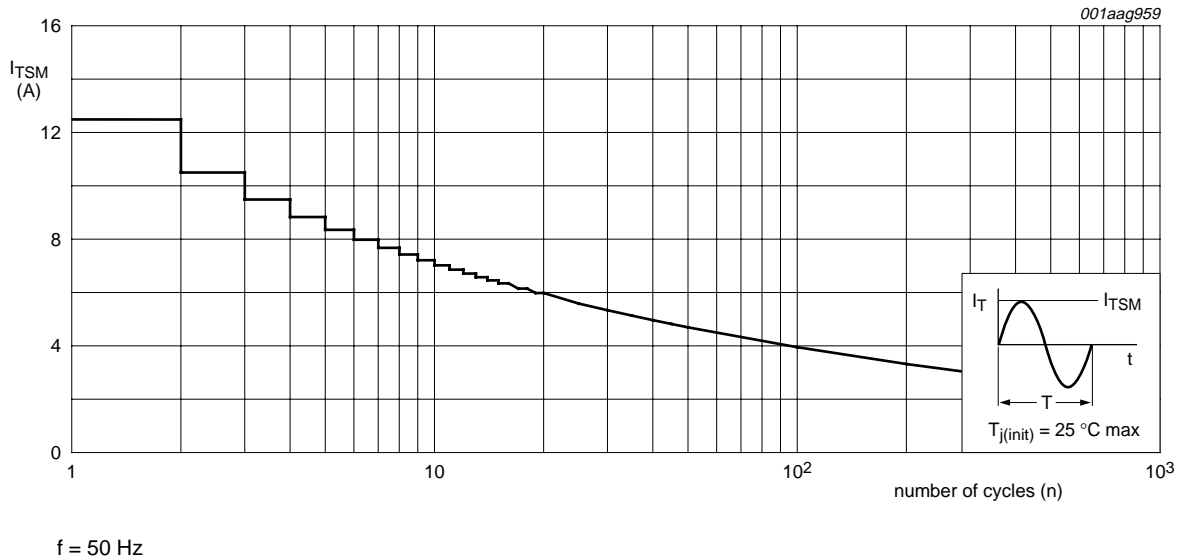
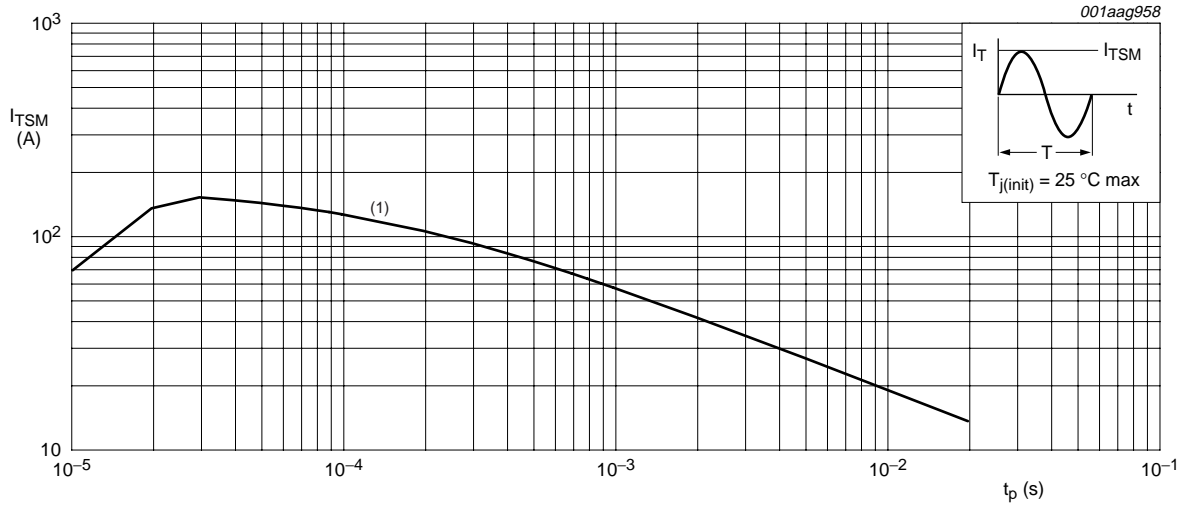


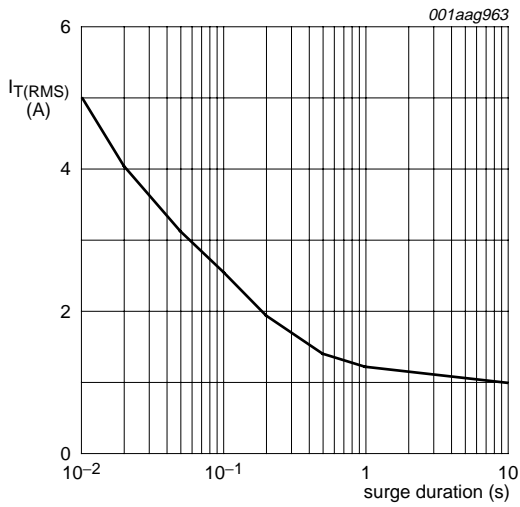
Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20\text{ ms}$

(1) di_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



$f = 50\text{ Hz}; T_{sp} = 106\text{ °C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

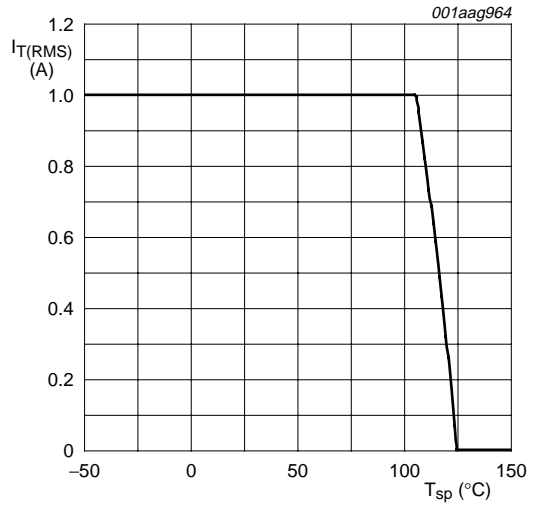


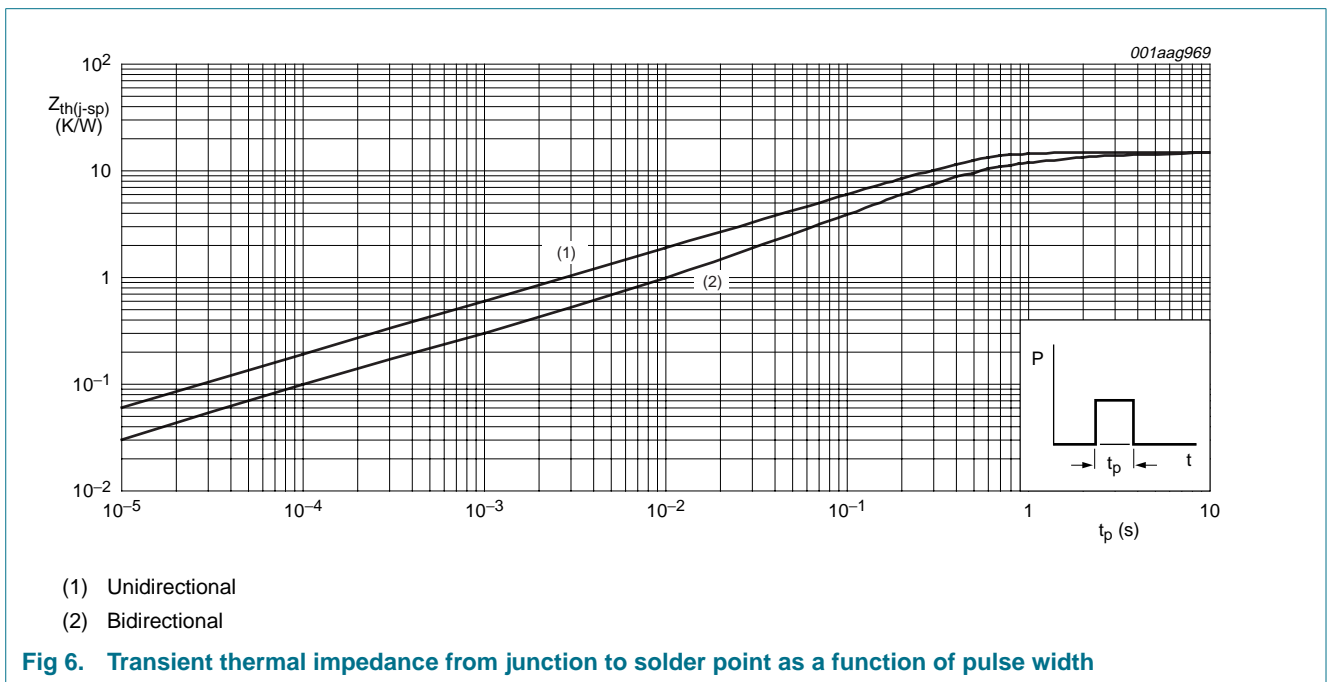
Fig 5. RMS on-state current as a function of solder point temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; see Figure 14	[1] -	156	-	K/W
		for pad area; see Figure 15	[1] -	70	-	K/W

[1] Mounted on a printed-circuit board.



6. Static characteristics

Table 5. Static characteristics

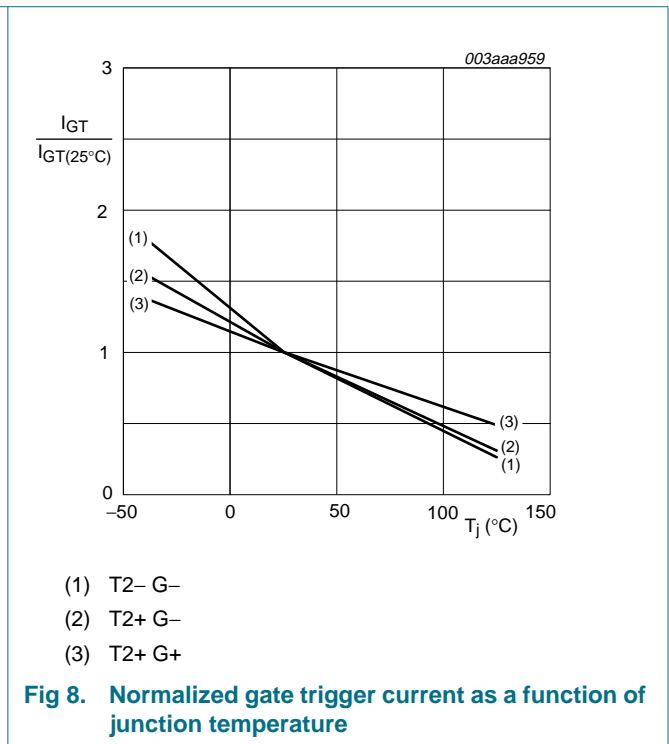
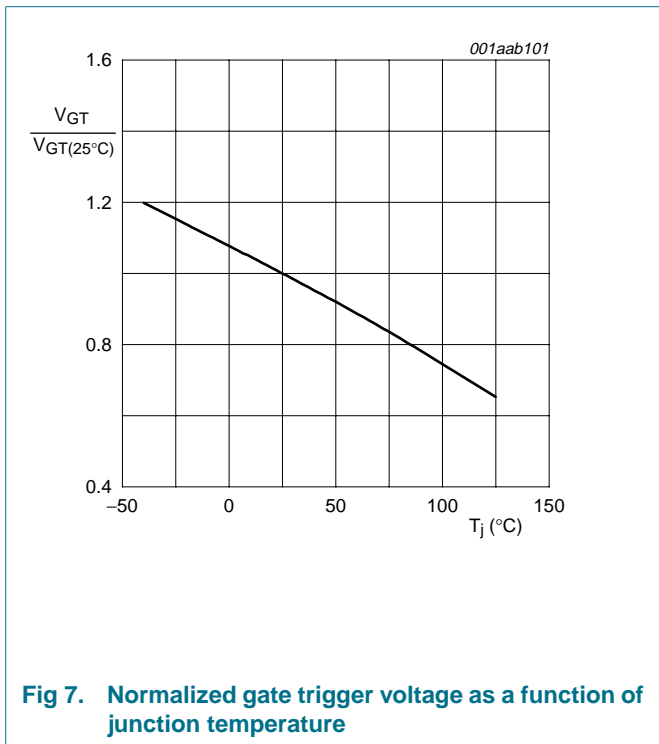
$T_j = 25\text{ °C}$ unless otherwise specified.

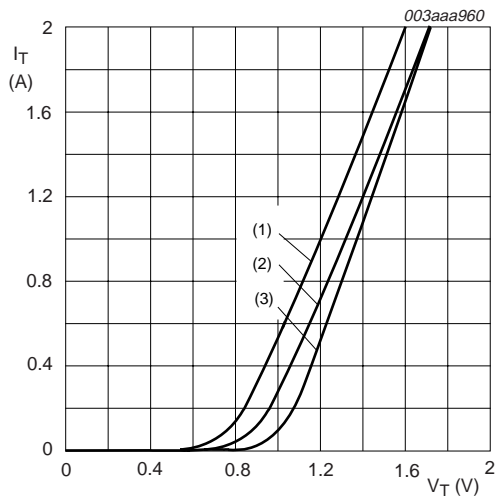
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BTA201W-600E and BTA201W-800E						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 8				
		T2+ G+	-	-	10	mA
		T2+ G-	-	-	10	mA
		T2- G-	-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; see Figure 10				
		T2+ G+	-	-	12	mA
		T2+ G-	-	-	20	mA
		T2- G-	-	-	12	mA
I_H	holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; see Figure 11	-	-	12	mA
V_T	on-state voltage	$I_T = 1.4\text{ A}$; see Figure 9	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 7	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.2	0.3	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
BTA201W-600E and BTA201W-800E						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	600	-	-	V/ μs
di_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 4\text{ A}$; gate open circuit				
		$dV_{com}/dt = 20\text{ V}/\mu\text{s}$	2.5	-	-	A/ms
		$dV_{com}/dt = 10\text{ V}/\mu\text{s}$	3.5	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs





$V_o = 1.02 \text{ V}; R_s = 358 \text{ m}\Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

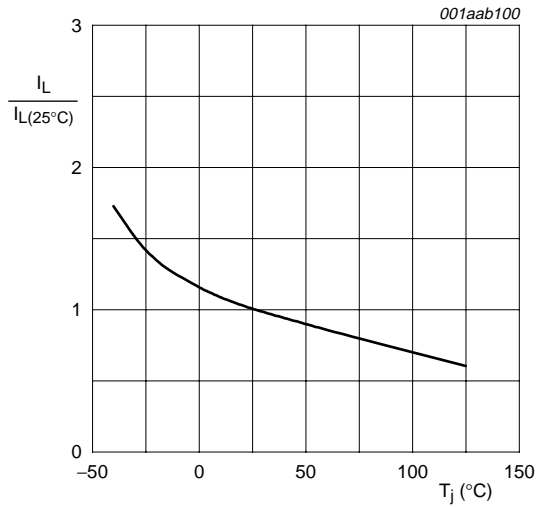


Fig 10. Normalized latching current as a function of junction temperature

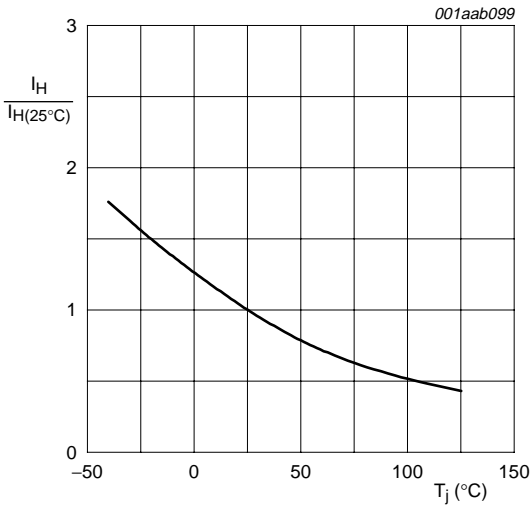
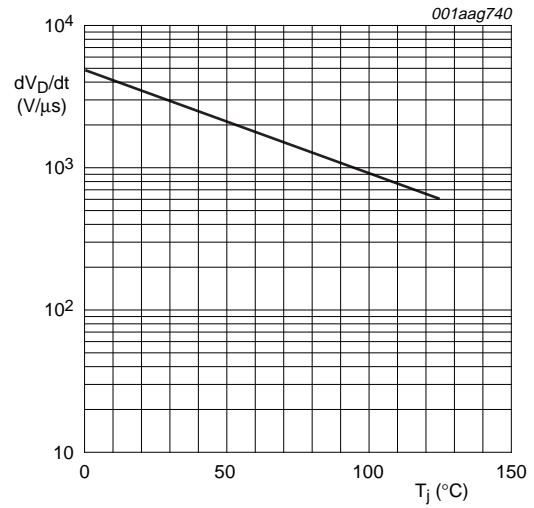


Fig 11. Normalized holding current as a function of junction temperature



Gate open circuit

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

8. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223

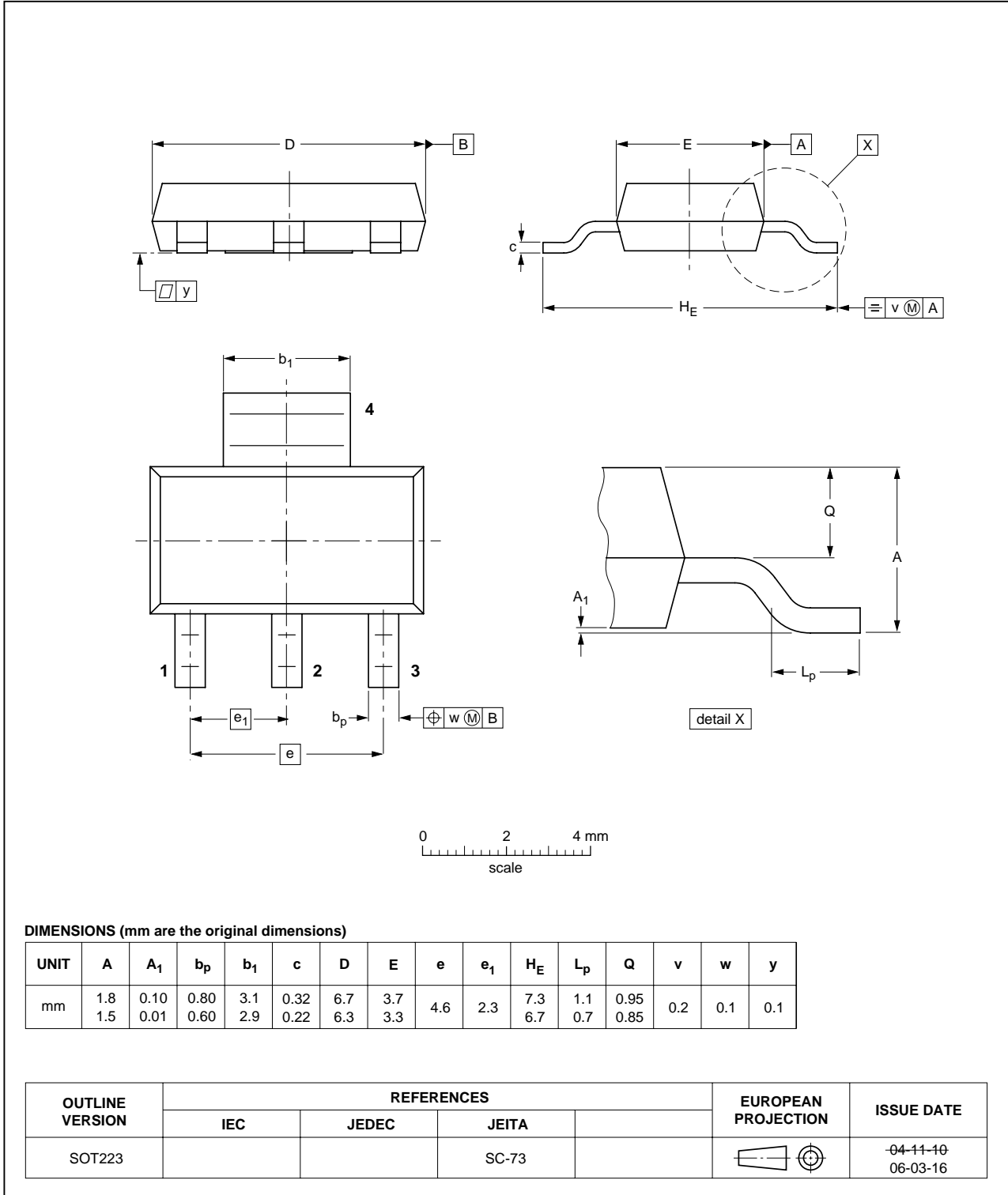
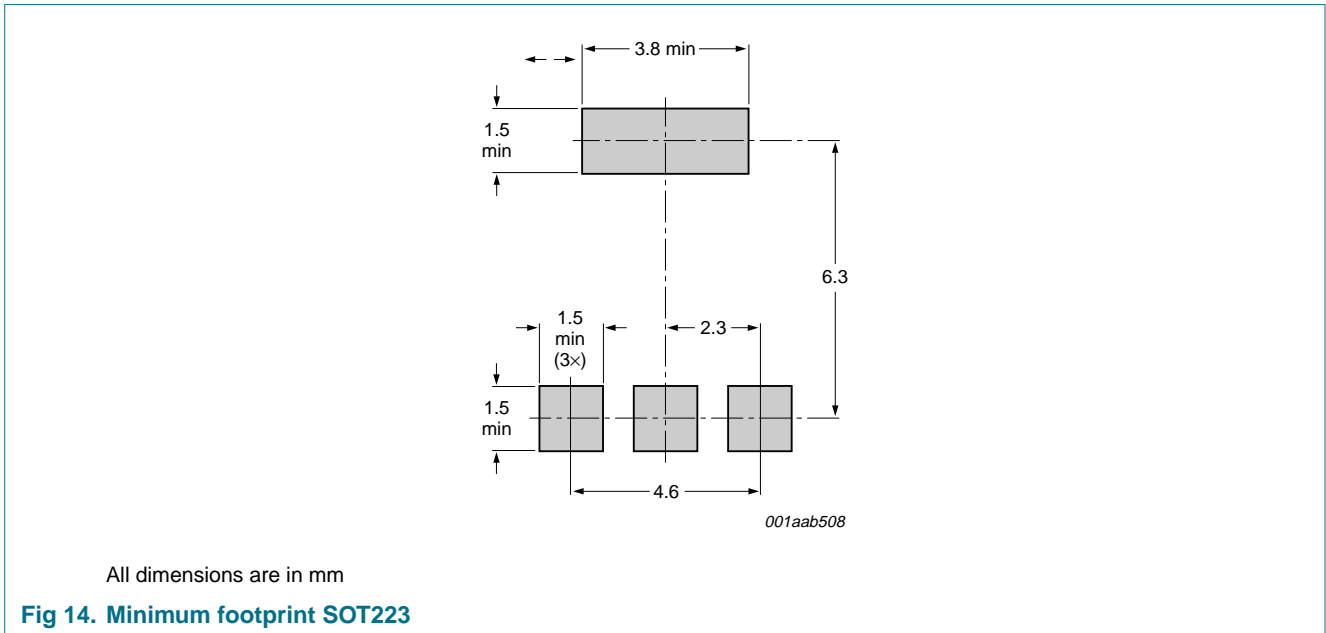


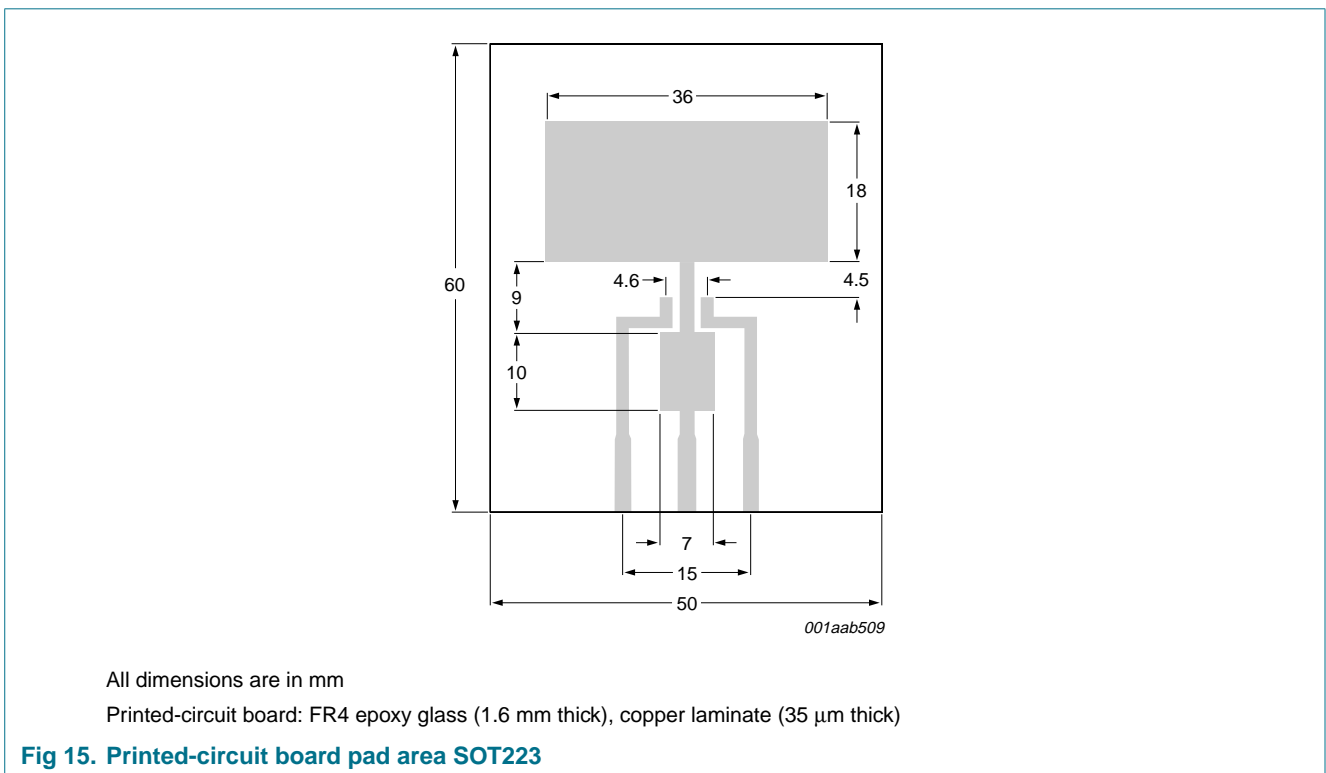
Fig 13. Package outline SOT223

9. Mounting

9.1 Mounting instructions



9.2 Printed-circuit board



10. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA201W_SER_E_2	20070917	Product data sheet	-	BTA201W_SER_E_1
Modifications:	<ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Descriptive titles have been corrected. • Table 3 “Limiting values” on page 2: di_T/dt updated • Table 6 “Dynamic characteristics” on page 7: dV_D/dt updated • Figure 12 “Critical rate of rise of off-state voltage as a function of junction temperature; minimum values” on page 8: graph updated 			
BTA201W_SER_E_1	20060207	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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